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Phase Control Thyristors (Hockey PUK Version), 910 A



TO-200AC (B-PUK)

PRODUCT SUMMARY					
Package	TO-200AC (B-PUK)				
Diode variation	Single SCR				
I _{T(AV)}	910 A				
V _{DRM} /V _{RRM}	1200 V, 1600 V, 1800 V, 2000 V				
V_{TM}	1.80 V				
I _{GT}	100 mA				
T_J	-40 °C to 125 °C				

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AC (B-PUK)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
,		910	A				
I _{T(AV)}	T _{hs}	55	°C				
		1857	A				
I _{T(RMS)}	T _{hs}	25	°C				
L	50 Hz	15 700	A				
I _{TSM}	60 Hz	16 400	^				
l ² t	50 Hz	1232	kA ² s				
I ² t	60 Hz	1125	KA-5				
V _{DRM} /V _{RRM}		1200 to 2000	V				
t _q	Typical	150	μs				
TJ		-40 to 125	°C				

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE VDRM/VRRM, MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V		V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA					
	12	1200	1300						
VS-ST700CL	16	1600	1700	80					
V3-31700CL	18	1800	1900	00					
	20	2000	2100						



ABSOLUTE MAXIMUM RATINGS	3					
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	L	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	1857	
		t = 10 ms	No voltage		15 700	
Maximum peak, one-cycle	1	t = 8.3 ms	reapplied		16 400	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		13 200	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	13 800	
Maximum I ² t for fusing		t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	1232	
	l ² t	t = 8.3 ms			1125	
		t = 10 ms			871	
		t = 8.3 ms	reapplied		795	
Maximum $I^2\sqrt{t}$ for fusing	I ² √t	t = 0.1 to 10) ms, no voltage	reapplied	12 321	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$), $T_J = T_J$ maximum	1.00	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.40	mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.35	11152
Maximum on-state voltage	V_{TM}	I _{pk} = 2000 A, T _J = T _J maximum, t _p = 10 ms sine pulse			1.80	V
Maximum holding current	Ι _Η	T. – 25 °C	T 05 °C and a sumble 10 V and the land			mA
Typical latching current	lμ	T _J = 25 °C, anode supply 12 V resistive load			1000	IIIA

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs		
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0			
Typical turn-off time	t _q	I_{TM} = 750 A, T_J = T_J maximum, dI/dt = 60 A/ μ s, V_R = 50 V, dV/dt = 20 V/ μ s, gate 0 V 100 Ω , t_p = 500 μ s	150	μs		

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	80	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	
FANAMETEN	STWIDOL	I Ex	TEST CONDITIONS			UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10	0.0	W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \; ms$	3	.0	Α
Maximum peak positive gate voltage	+V _{GM}	T. – T. maximum	t < 5 ms	20		V
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			5.0	
		T _J = -40 °C	Maximum required gate	200	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	200	mA
		T _J = 125 °C	trigger/ current/voltage are the lowest	50	-	
		T _J = -40 °C	value which will trigger all units	2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.8	3.0	V
		T _J = 125 °C		1.1	-	
DC gate current not to trigger	I _{GD}	T T managina uma	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.:	25	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	T_J		-40 to 125	°C	
Maximum storage temperature range	T _{Stg}		-40 to 150		
Maximum thermal registance, junction to heataink	р	DC operation single side cooled	0.073		
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.031	K/W	
Maximum thermal resistance, case to heatsink	R _{thC-hs}	DC operation single side cooled	0.011	T N V V	
Maximum thermal resistance, case to neatsink		DC operation double side cooled	0.006		
Mounting force, ± 10 %			14 700 (1500)	N (kg)	
Approximate weight			255	g	
Case style		See dimensions - link at the end of datasheet	TO-200AC (B-PUK)	

△R _{thJ-hs} CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	LIMITO	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	1EST CONDITIONS	UNITS	
180°	0.009	0.009	0.006	0.006	$T_J = T_J$ maximum		
120°	0.011	0.011	0.011	0.011			
90°	0.014	0.014	0.015	0.015		K/W	
60°	0.020	0.020	0.021	0.021			
30°	0.036	0.036	0.036	0.036			

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC



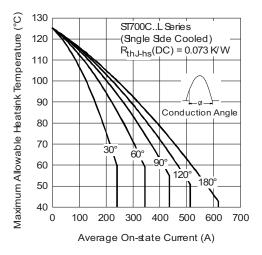


Fig. 1 - Current Ratings Characteristics

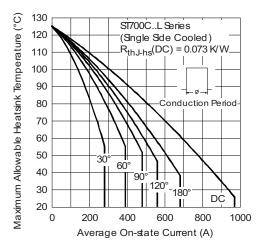


Fig. 2 - Current Ratings Characteristics

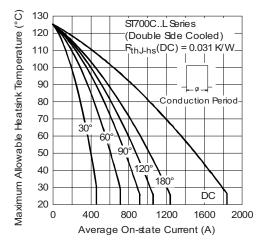


Fig. 3 - Current Ratings Characteristics

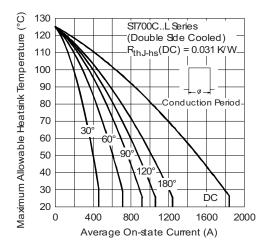


Fig. 4 - Current Ratings Characteristics

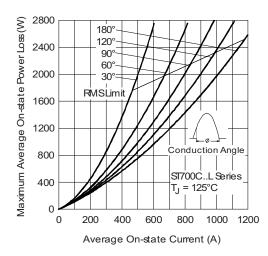


Fig. 5 - On-State Power Loss Characteristics

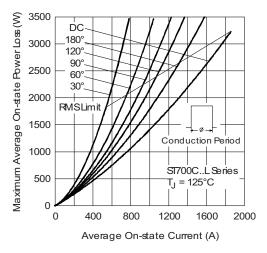


Fig. 6 - On-State Power Loss Characteristics

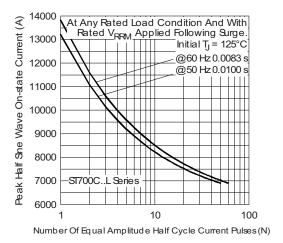


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

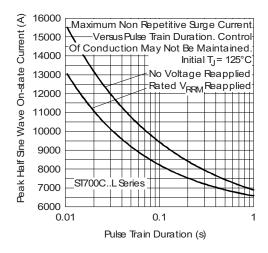


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

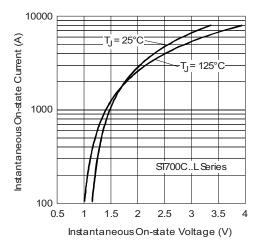


Fig. 9 - On-State Voltage Drop Characteristics

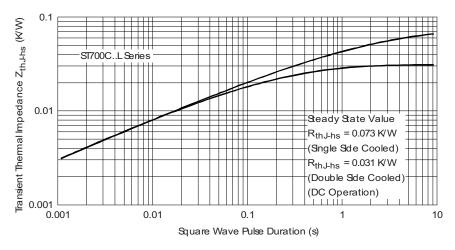


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

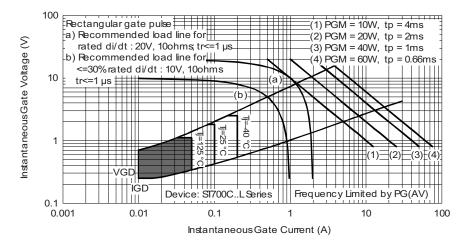
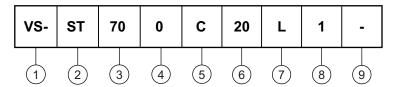


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

7 - L = PUK case TO-200AC (B-PUK)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

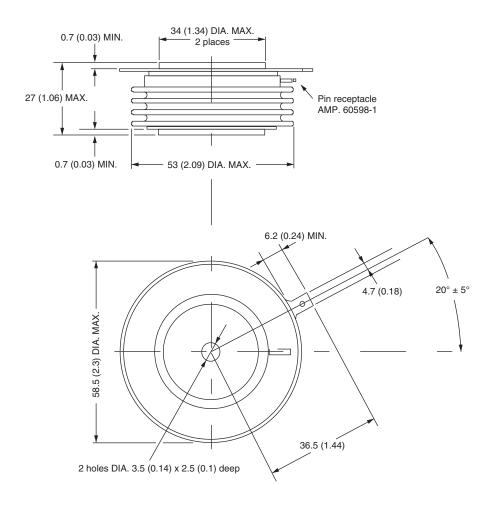
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95076			



TO-200AC (B-PUK)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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